AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-61 (Canceled).

Claims 62-69 (Canceled).

70. (Previously Presented) A nitride semiconductor light emitting device comprising:

a substrate,

a first nitride semiconductor layer being undoped and being a single layer,

a second nitride semiconductor layer having an n-type electrode and being a single layer,

a third nitride semiconductor layer being a super lattice layer of GaN layers, and

a separate and distinct active layer where electrons and holes are combined.

71. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer is made of GaN or AlGaN and said second nitride semiconductor layer includes Si as an n-type impurity.

72. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said first nitride semiconductor layer is made of GaN or AlGaN

73. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer has an carrier concentration more than $3 \times 10^{18}/cm^3$.

74. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer has a resistivity less than 8×10^{-3} ohm · cm.

75. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

further comprising a buffer layer between said substrate and said first nitride semiconductor layer.

76. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said first nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm,

77. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm.

78. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said third nitride semiconductor layer being a super lattice layer of undoped GaN layers and Si doped GaN layers.

79. (Previously Presented) The nitride semiconductor light emitting device according to claim 78;

wherein said Si doped GaN layers are doped with Si to $1x10^{19}/cm^3$.

80. (Previously Presented) The nitride semiconductor light emitting device according to claim 78;

wherein said undoped GaN layers have a thickness of 75Å and Si doped GaN layers have a thickness of 25Å.

81. (Previously Presented) The nitride semiconductor light emitting device according to claim 78;

wherein said third nitride semiconductor layer has a thickness of 600Å.